

### WS4611

#### $80m\Omega$ , Current Limited, Power Distribution Switch

### Descriptions

The WS4611 is high-side switch with ultra-low ON resistance P-MOSFET. Integrated current-limit function can limit inrush current for heave capacitive load, over load current, and short-circuit current to protect power source.

The WS4611 is also integrated reverse protection function to eliminate any reverse current flow across the switch when the device is off. Thermal shutdown function can protect the device and load. The output auto-discharge function is disabled in WS4611.

The WS4611 is available in SOT-23-5L package. Standard product is Pb-free and Halogen-free.

### Features

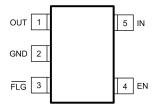
- Input voltage range : 2.5~5.5V
- Main switch R<sub>ON</sub>
- : 80mΩ @ V<sub>IN</sub>=5V
- Current limit threshold
  - WS4611EB : 1.0A (Typ.)
- Reverse block (No "body diode")
- Over temperature protection

### Applications

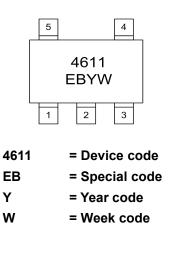
- USB peripherals
- USB Dongle
- USB 3G data card
- 3.3V or 5V Power Switch
- 3.3V or 5V Power Distribution

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### Pin configuration (Top view)



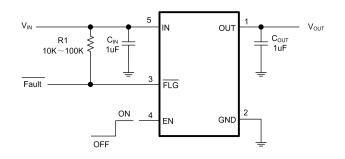
Marking

### **Order information**

Device	Package	Shipping
WS4611EB-5/TR	SOT-23-5L	3000/Reel&Tape



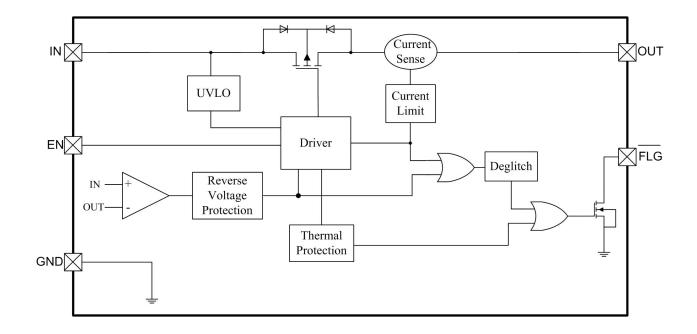
## **Typical Applications**



## **Pin Descriptions**

Pin Number	Symbol	Descriptions			
1	OUT	Output Pin			
2	GND	Ground			
3	FLG	Fault Flag Pin, Open-Drain, Active Low			
4	EN	Enable Pin, Active High			
5	IN	Input Pin			

# **Block Diagram**





### Absolute maximum ratings

Parameter	Symbol	Value	Unit
IN pin voltage range	VIN	-0.3~6.5	<
OUT pin voltage range	Vout	-0.3~6.5	>
FLG pin voltage range	VFLG	-0.3~6.5	>
EN pin voltage range	VEN	-0.3~6.5	>
Junction temperature	TJ	-40~150	о°
Lead temperature(Soldering, 10s)	TL	260	о°
Storage temperature	Tstg	-55 ~ 150	о°
IN OUT Din ESD Datings	HBM	8000	V
IN, OUT Pin ESD Ratings	MM	400	V
FLG, EN Pin ESD Ratings	HBM	4000	V
	MM	400	V

These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

## **Recommend Operating Conditions**

Parameter	Symbol	Value	Unit
Supply input voltage range	V <sub>IN</sub>	2.5~5.5	V
Operating ambient temperature	T <sub>A</sub>	-40~85	°C
Thermal Resistance	R <sub>0JA</sub>	250	°C/W



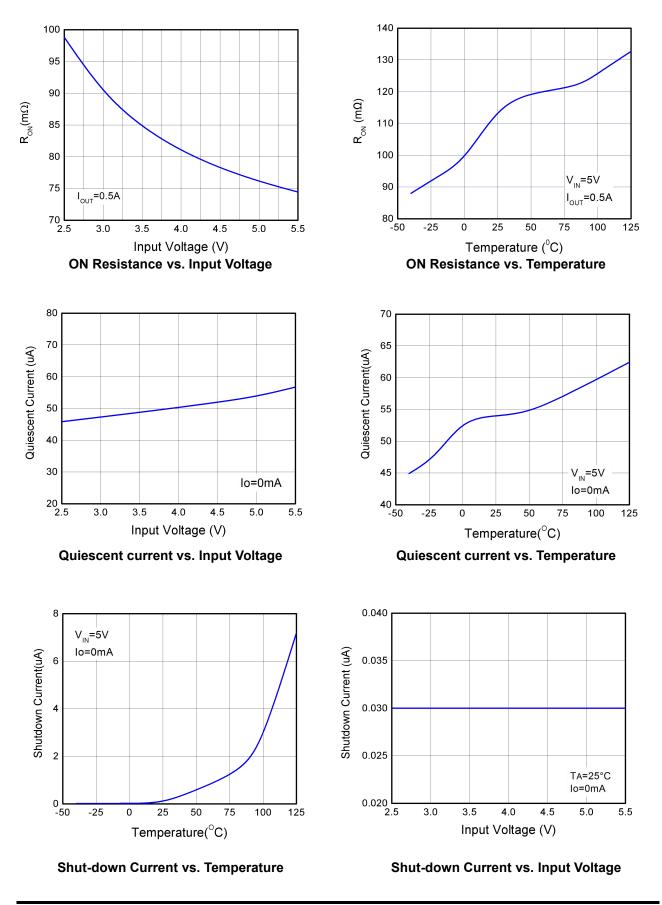
## Electronics Characteristics (Ta=25°C, V<sub>IN=5</sub>V, C<sub>IN=</sub>C<sub>OUT</sub>=1µF, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Quiescent supply current	lq	I <sub>OUT</sub> =0, V <sub>IN</sub> =V <sub>EN</sub> =5V		48	60	μA
Shutdown current	I <sub>SD</sub>	V <sub>EN</sub> =0V			1	μA
Reverse current	I <sub>REV</sub>	$V_{IN}=V_{EN}=0V$ , $V_{OUT}=5V$ , Current flow to $V_{IN}$			1	μA
Main-FET ON resistance <sup>(1)</sup>	R <sub>ON</sub>	V <sub>IN</sub> =V <sub>EN</sub> =5V, I <sub>OUT</sub> =500mA		80		mΩ
Auto-discharge FET ON resistance	RDCHG	V <sub>EN</sub> =0V, V <sub>IN</sub> =V <sub>OUT</sub> =5V		65		Ω
Over-current trip threshold	loc	Current ramp (≤100A/s) on OUT	0.7	1	1.4	A
Short-circuit output current	los	OUT shorted to GND		0.45		A
Short circuit current limiting response time	tshort	OUT connected to GND, $C_L=1\mu F$		2		μs
EN input low voltage	VIL	VIN=5V			0.4	V
EN input high voltage	VIH	VIN=5V	1.6			V
OUT pin turn-on time after EN ON	t <sub>ON</sub>	$C_L=1\mu F$ , $R_L=50hm$		20		μs
Fault flag output blanking time	t <sub>BLANK</sub>			9		ms
Over-temperature shutdown threshold	T <sub>SD</sub>			160		°C
Over-temperature threshold hysteresis	T <sub>HYS</sub>			35		°C
Under voltage lock out threshold	V <sub>UVLO</sub>			2.2		V
Under voltage lock out hysteresis	V <sub>UVLO-HYS</sub>			200		mV

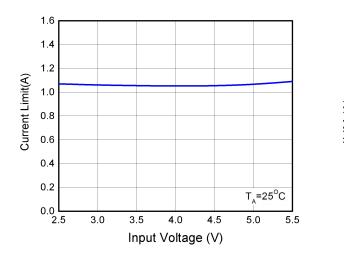
Note: (1) Pulse test,  $T_P$ =380us



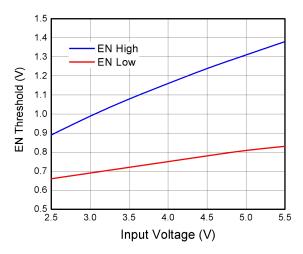
### Typical Characteristics (Ta=25°C, unless otherwise noted)



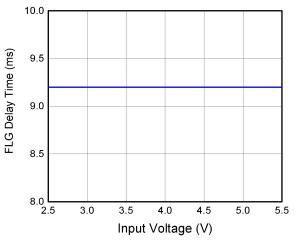




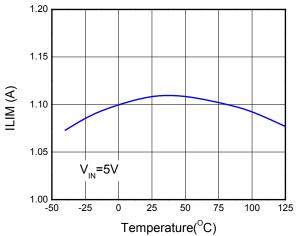




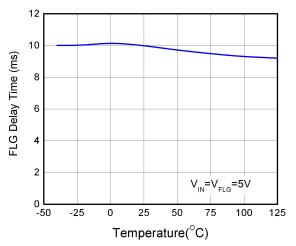
EN Threshold vs. Input Voltage



Fault Flag Blanking time vs. Input Voltage



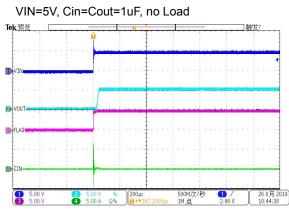
Current Limit vs. Temperature



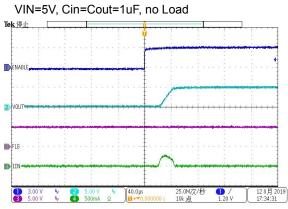
Fault Flag Blanking time vs. Temperature



#### Startup from Power ON

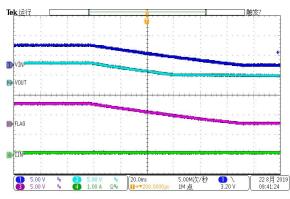


### Startup from Enable ON

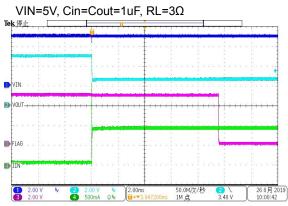


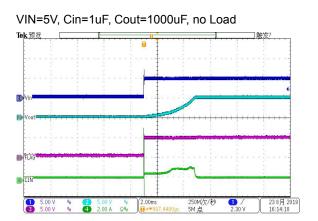
#### Shutdown from Power OFF

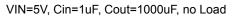
VIN=5V, Cin=Cout=1uF, no Load

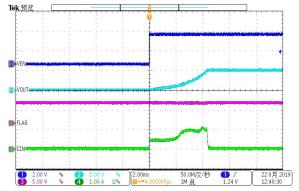


### **Current Limit Response**

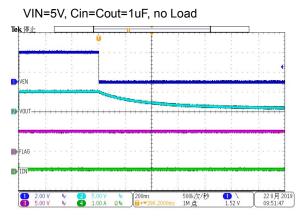




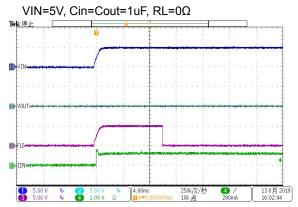




#### Shutdown from Enable OFF



## Start into Short Circuit



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### **Operation Information**

### **Power Switch**

The power switch is an P-channel MOSFET with low  $R_{DS(ON)}$  for power management or USB power distribution applications. The WS4611 has reverse voltage protection to prevents current flow from OUT to IN and IN to OUT when device is off.

### **Current-Limit Protection**

The WS4611 provide current limit protection function to protect power source when over-current condition occurs.

### **Short-Circuit Protection**

The WS4611 provide short circuit protection function. The output current will be limited to safe level. The short-circuit protection is used to reduce power dissipation of the device and protect power source during short-circuit condition.

### Fault indicate

The FLG open drain output is asserted (active low) with 8ms(Typ.) delay when an over-current or over-temperature condition is encountered. The FLG signal will remain asserted until the over-current or over-temperature condition is removed.

#### **UVLO Protection**

To avoid malfunction of the WS4611 at low input voltages, an under voltage lockout is included that disables the device, until the input voltage exceeds 2.2V (Typ.).

#### Shutdown Mode

Drive EN to GND to place the WS4611 in shutdown mode. In shutdown mode, input current falls to smaller than 1uA.

#### Thermal Shutdown

As soon as the junction temperature (T<sub>J</sub>) exceeds 160°C (Typ.), the WS4611 goes into thermal shutdown. In this mode, the device is turned off and will turn on again until Junction temperature falls below 125°C (Typ.).



## **Application Information**

### **Output Capacitor**

the device.

A low ESR, 150uF aluminum electrolytic or tantalum between OUT and GND is strongly recommended to reduce the voltage droop during hot-plug of downstream peripheral. Higher value output capacitor is better when the output load is heavy. Additionally, bypassing the output with a 1uF ceramic capacitor improves the immunity of the device to short-circuit transients.

### PCB Layout consideration

The PCB layout should be carefully performed to maximize thermal dissipation and to minimize voltage drop. The following guidelines must be considered:

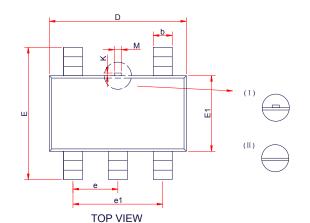
1. Please place the input capacitors near the IN pin as close as possible.

- 2. Output decoupling capacitors for load must be placed near the load as close as possible for decoupling high frequency ripples.
- 3. Locate WS4611 and output capacitors near the load to reduce parasitic resistance and inductance for excellent load transient performance.
- 4. The negative pins of the input and output capacitors and the GND pin must be connected to the ground plane of the load.
- 5. Keep IN and OUT traces as wide and short as possible.



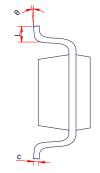
## PACKAGE OUTLINE DIMENSIONS

SOT-23-5L

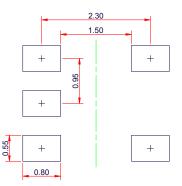


A

R



SIDE VIEW



SIDE VIEW

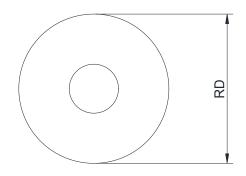
RECOMMENDED LAND PATTERN (unit: mm)

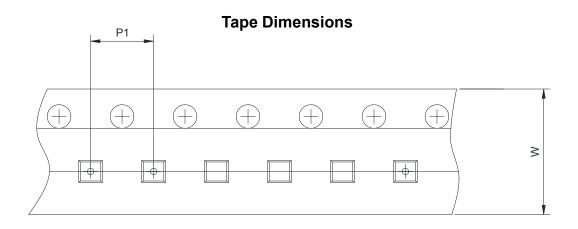
Cumhal	Dimensions in Millimeters					
Symbol	Min.	Тур.	Max.			
A			1.45			
A1	0.00	-	0.15			
A2	0.90	1.10	1.30			
b	0.30	0.40	0.50			
с	0.10	-	0.21			
D	2.72	2.92	3.12			
E	E 2.60 2.80		3.00			
E1	1.40	1.60	1.80			
е	0.95 BSC					
e1	1.90 BSC					
L	0.30	0.45	0.60			
М	0.10	0.15	0.25			
К	0.00	-	0.25			
θ	<b>0</b> °	- 8°				



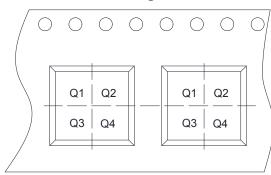
### TAPE AND REEL INFORMATION

### **Reel Dimensions**





# **Quadrant Assignments For PIN1 Orientation In Tape**





User Direction of Feed

RD	Reel Dimension	🗹 7inch	🔲 13inch		
W	Overall width of the carrier tape	🗹 8mm	🔲 12mm	🔲 16mm	
P1	Pitch between successive cavity centers	🔲 2mm	🗹 4mm	🔲 8mm	
Pin1	Pin1 Quadrant	🗖 Q1	🗖 Q2	<b>✓</b> Q3	🗖 Q4

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